

TIGER ELECTRONIC CO.,LTD

SOT-23 Plastic-Encapsulate Transistors

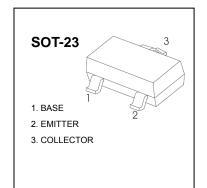
\$8050 TRANSI STOR (NPN)

FEATURES

Complimentary to S8550
Collector Current: I_C=0.5A

MARKING: J3Y

MAXIMUM RATINGS (Ta=25℃ unless otherwise noted)



Symbol	Parameter	Value	Unit	
V _{CBO}	Collector-Base Voltage	40	V	
V _{CEO}	Collector-Emitter Voltage	25	V	
V _{EBO}	Emitter-Base Voltage	5	V	
Ic	Collector Current -Continuous	0.5	Α	
Pc	Collector Dissipation	0.3	W	
Tj	Junction Temperature	150	°C	
T _{stg}	Storage Temperature	-55-150	°C	

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 100μA, I _E =0	40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =1mA, I _B =0	25			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5			V
Collector cut-off current	Ісво	V _{CB} =40 V , I _E =0			0.1	μΑ
Collector cut-off current	Iceo	V _{CB} =20V , I _E =0			0.1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 5V , I _C =0			0.1	μА
DC current gain	H _{FE(1)}	V _{CE} =1V, I _C = 50mA	120		350	
DC current gain	H _{FE(2)}	V _{CE} =1V, I _C = 500mA	50			
Collector-emitter saturation voltage	V _{CE} (sat)	I=500 mA, I _B = 50mA			0.6	V
Base-emitter saturation voltage	V _{BE} (sat)	I _C =500 mA, I _B = 50mA			1.2	V
Transition frequency	f _T	V _{CE} =6V, I _C = 20mA f=30MHz	150			MHz

CLASSIFICATION OF h_{FE(1)}

Rank	L	Н
Range	120-200	200-350

Typical Characterisitics

S8050

